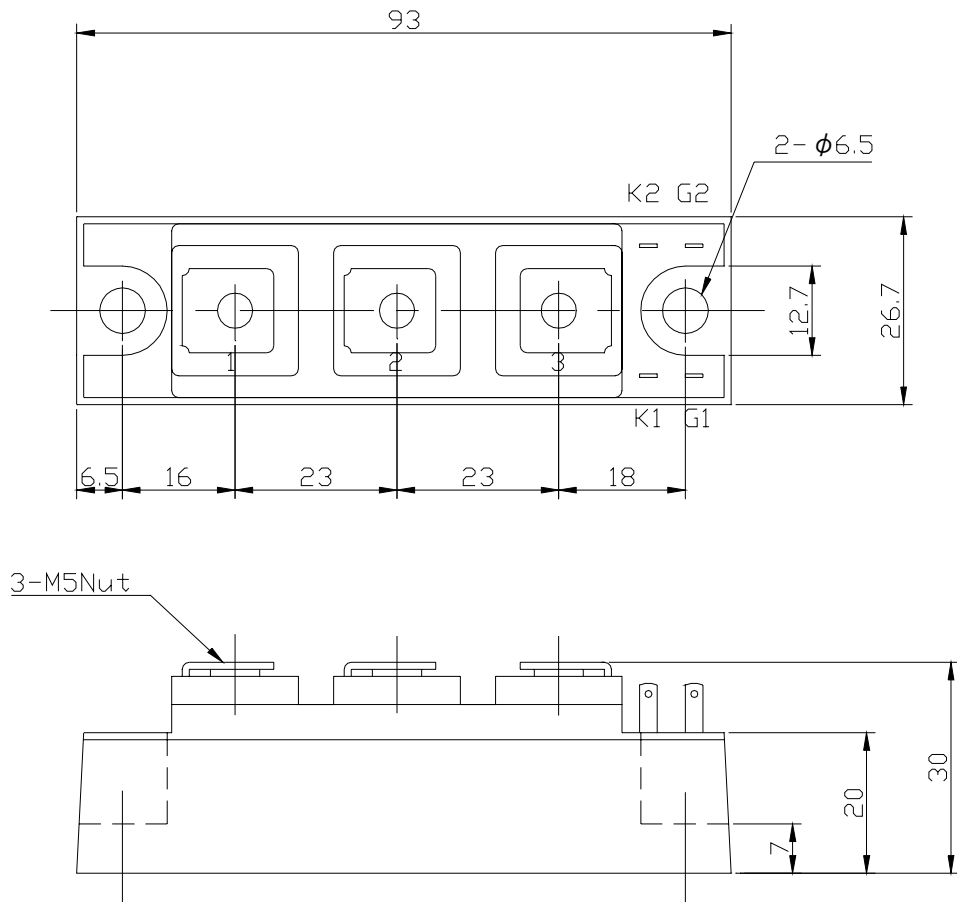


Electrical • Thermal Characteristics

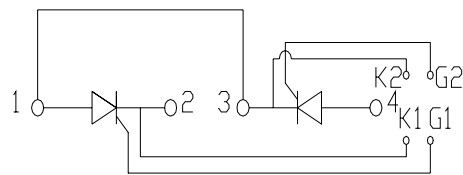
Characteristics	Symbol	Test Conditions	Maximum Value.			Unit
			Min.	Typ.	Max.	
Peak Off-State Current	I_{DM}	$V_{DM} = V_{DRM}, T_j = 125^\circ\text{C}$			20	mA
Peak Reverse Current	I_{RM}	$V_{RM} = V_{RRM}, T_j = 125^\circ\text{C}$			20	mA
Peak Forward Voltage	V_{TM}	$I_{TM} = 300\text{A}, T_j = 25^\circ\text{C}$			1.38	V
Gate Current to Trigger	I_{GT}	$V_D = 6\text{V}, I_T = 1\text{A}$	$T_j = -40^\circ\text{C}$		200	mA
			$T_j = 25^\circ\text{C}$		100	
			$T_j = 125^\circ\text{C}$		50	
Gate Voltage to Trigger	V_{GT}	$V_D = 6\text{V}, I_T = 1\text{A}$	$T_j = -40^\circ\text{C}$		4	V
			$T_j = 25^\circ\text{C}$		2.5	
			$T_j = 125^\circ\text{C}$		2	
Gate Non-Trigger Voltage	V_{GD}	$V_D = 2/3V_{DRM}, T_j = 125^\circ\text{C}$	0.25			V
Critical Rate of Rise of Off-State Voltage	dv/dt	$V_D = 2/3V_{DRM}, T_j = 125^\circ\text{C}$	500			V/ μs
Turn-Off Time	tq	$I_{TM} = I_o, V_D = 2/3V_{DRM}$ $dv/dt = 20\text{V}/\mu\text{s}, V_R = 100\text{V}$ $-di/dt = 20\text{A}/\mu\text{s}, T_j = 125^\circ\text{C}$		100		μs
Turn-On Time	tgt	$V_D = 2/3V_{DRM}, T_j = 125^\circ\text{C}$ $I_G = 200\text{mA}, di_G/dt = 0.2\text{A}/\mu\text{s}$		6		μs
Delay Time	td			2		μs
Rise Time	tr			4		μs
Latching Current	I_L	$T_j = 25^\circ\text{C}$		100		mA
Holding Current	I_H	$T_j = 25^\circ\text{C}$		50		
Thermal Resistance	Rth(j-c)	Junction to Case			0.35	$^\circ\text{C}/\text{W}$
	Rth(c-f)	Base Plate to Heat Sink with Thermal Compound			0.2	

Value Per 1Arm

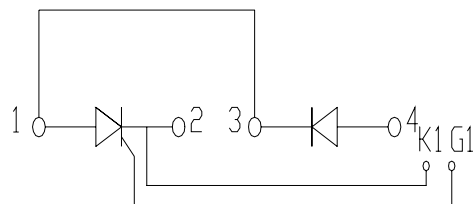
PDT/PDH1001x OUTLINE DRAWING (Dimensions in mm)



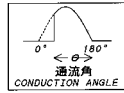
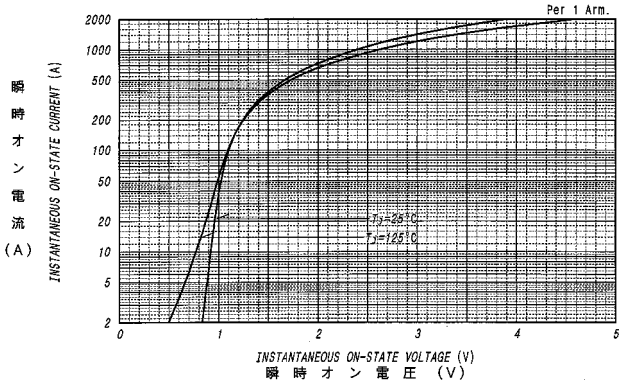
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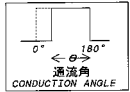
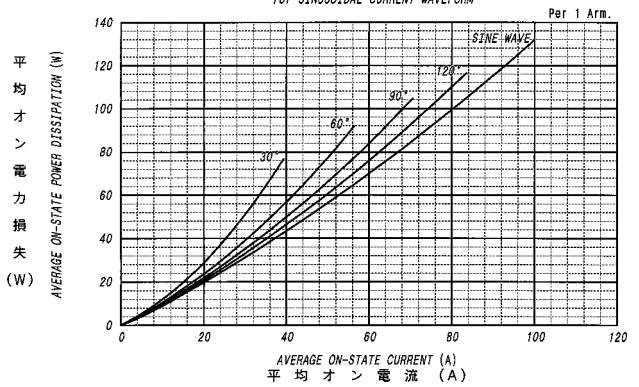
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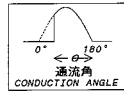
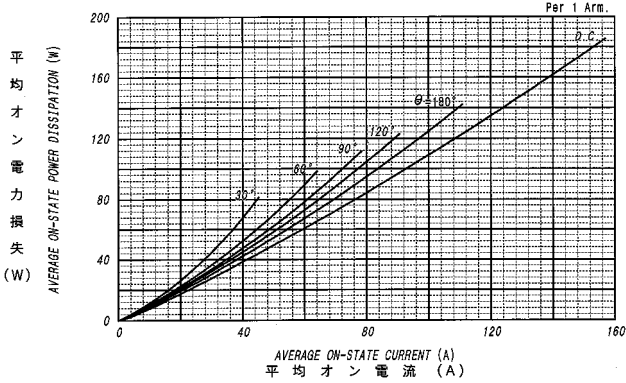
オン電圧特性
ON-STATE CURRENT VS. VOLTAGE



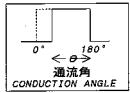
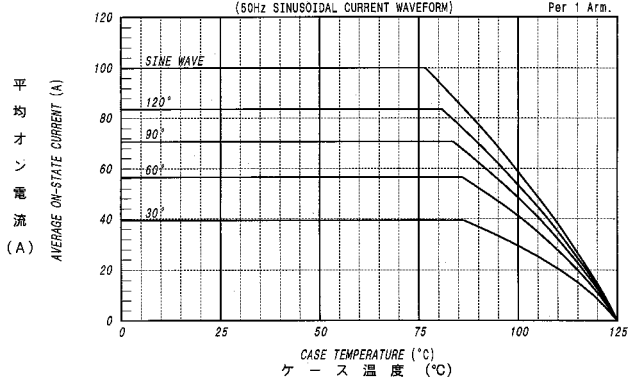
平均オン電力損失特性
AVERAGE ON-STATE POWER DISSIPATION
for SINUSOIDAL CURRENT WAVEFORM



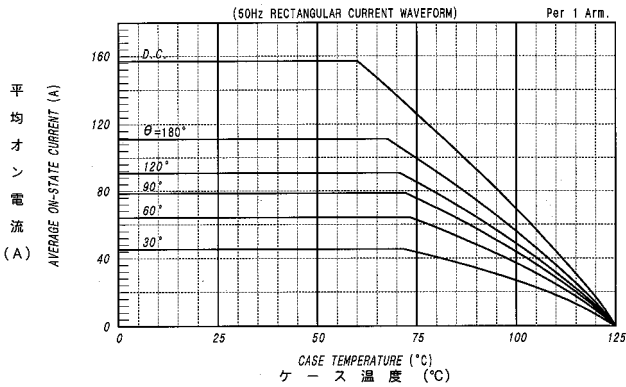
平均オン電力損失特性
AVERAGE ON-STATE POWER DISSIPATION
for RECTANGULAR CURRENT WAVEFORM



平均オン電流 - ケース温度定格
AVERAGE ON-STATE CURRENT VS. CASE TEMPERATURE

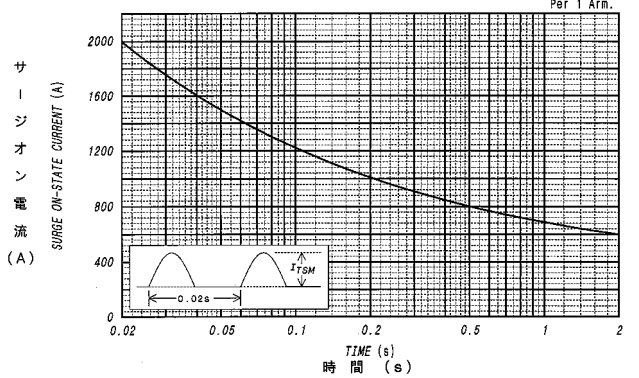


平均オン電流 - ケース温度定格
AVERAGE ON-STATE CURRENT VS. CASE TEMPERATURE

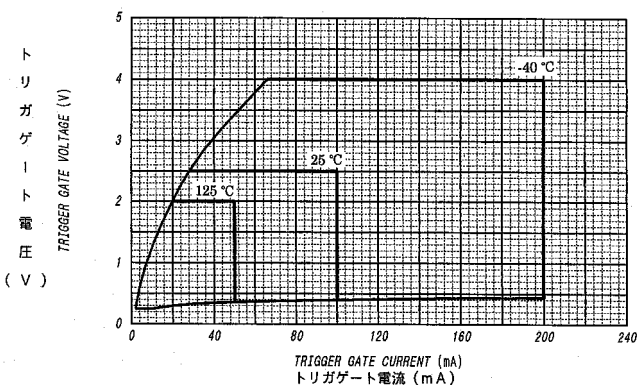


サージオン電流定格
SURGE CURRENT RATINGS

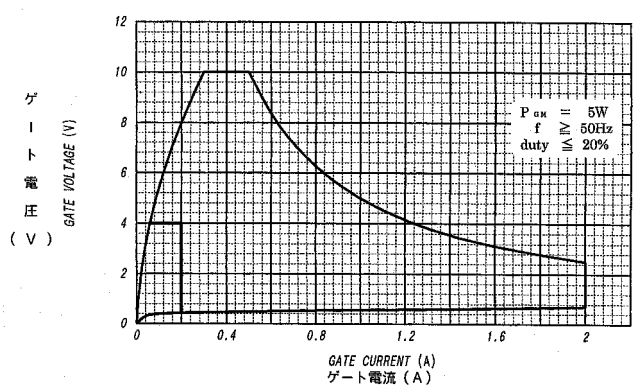
f=50Hz, Half Sine Wave, Non-Repetitive, Tj=125°C



ゲート特性
GATE CHARACTERISTICS



ゲート定格
GATE RATINGS



$P_{GM} = 5W$
 $f = 50Hz$
duty $\leq 20\%$

過渡熱抵抗特性
 MAXIMUM TRANSIENT THERMAL IMPEDANCE
 Junction to Case

